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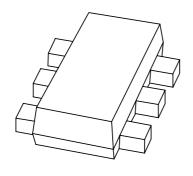
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Kind regards,

Team Nexperia

#### **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# **PBSS2515VS**15 V low V<sub>CE(sat)</sub> NPN double transistor

Product data sheet Supersedes data of 2001 Nov 07

2004 Dec 23



## 15 V low V<sub>CE(sat)</sub> NPN double transistor

#### PBSS2515VS

#### **FEATURES**

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- · Excellent coplanarity due to straight leads
- · Low collector-emitter saturation voltage
- · High current capability
- Improved thermal behaviour due to flat lead
- Replaces two SC-75/SC-89 packaged low V<sub>CEsat</sub> transistors on same PCB area
- · Reduces required PCB area
- · Reduced pick and place costs.

#### **APPLICATIONS**

- · General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- · Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

#### **DESCRIPTION**

NPN low  $V_{\text{CEsat}}$  double transistor in a SOT666 plastic package.

PNP complement: PBSS3515VS.

#### **MARKING**

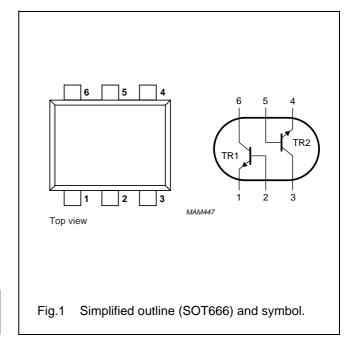
TYPE NUMBER	MARKING CODE
PBSS2515VS	N9

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	15	V
I <sub>CM</sub>	peak collector current	1	Α
R <sub>CEsat</sub>	equivalent on-resistance	<500	mΩ

#### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



#### ORDERING INFORMATION

TYPE NUMBER PACKAGE			
TIPE NOMBER			VERSION
PBSS2515VS		plastic surface mounted package; 6 leads	SOT666

## 15 V low $V_{CE(sat)}$ NPN double transistor

PBSS2515VS

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT		
Per transis	Per transistor unless otherwise specified						
V <sub>CBO</sub>	collector-base voltage	open emitter	_	15	٧		
$V_{CEO}$	collector-emitter voltage	open base	_	15	٧		
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	٧		
I <sub>C</sub>	collector current (DC)		_	500	mA		
I <sub>CM</sub>	peak collector current		_	1	Α		
I <sub>BM</sub>	peak base current		_	100	mA		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	200	mW		
T <sub>stg</sub>	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C		
Per device	Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW		

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

#### **Notes**

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board.

## 15 V low $V_{\text{CE(sat)}}$ NPN double transistor

PBSS2515VS

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor unless otherwise specified						
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 15 V; I <sub>E</sub> = 0 A	-	_	100	nA	
		V <sub>CB</sub> = 15 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μΑ	
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A	-	-	100	nA	
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 10 mA	200	-	_		
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA; note 1	150	_	_		
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 500 mA; note 1	90	-	_		
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	25	mV	
	voltage	I <sub>C</sub> = 200 mA; I <sub>B</sub> = 10 mA	-	-	150	mV	
		$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	_	_	250	mV	
R <sub>CEsat</sub>	equivalent on-resistance	$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	-	300	<500	mΩ	
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	-	-	1.1	V	
$V_{BE}$	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA; note 1	_	_	0.9	V	
f <sub>T</sub>	transition frequency	$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	250	420	_	MHz	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	4.4	6	pF	

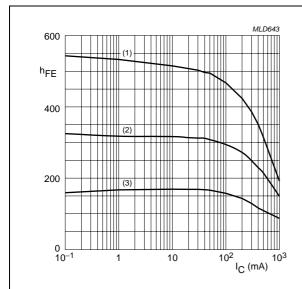
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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## 15 V low V<sub>CE(sat)</sub> NPN double transistor

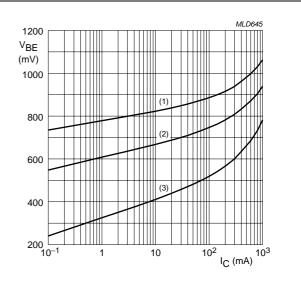
#### PBSS2515VS



V<sub>CE</sub> = 2 V.

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

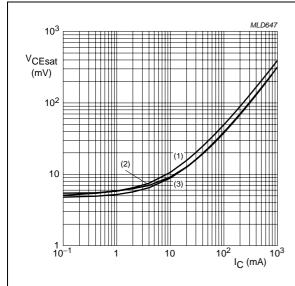
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 2 V$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

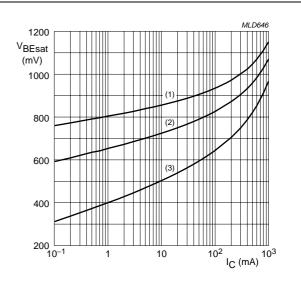
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



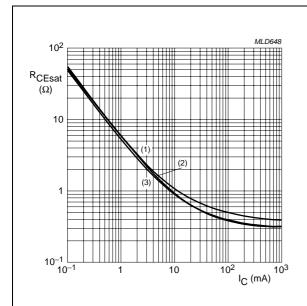
 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C.$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

## 15 V low $V_{\text{CE(sat)}}$ NPN double transistor

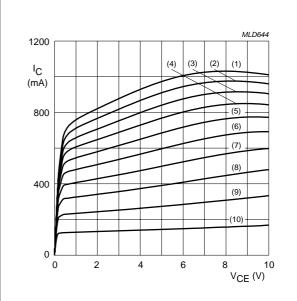
#### PBSS2515VS



 $I_{\rm C}/I_{\rm B}=20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C.$
- (3)  $T_{amb} = -55$  °C.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.



T<sub>amb</sub> = 25 °C.

- (1)  $I_B = 4.6 \text{ mA}.$
- (6)  $I_B = 2.3 \text{ mA}.$
- (2)  $I_B = 4.14 \text{ mA}.$
- (7)  $I_B = 1.84 \text{ mA}.$
- (3)  $I_B = 3.68 \text{ mA}.$
- (8)  $I_B = 1.38 \text{ mA}.$
- (4)  $I_B = 3.22 \text{ mA}.$
- (9)  $I_B = 0.92 \text{ mA}.$
- (5)  $I_B = 2.76 \text{ mA}.$
- (10)  $I_B = 0.46 \text{ mA}$ .

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

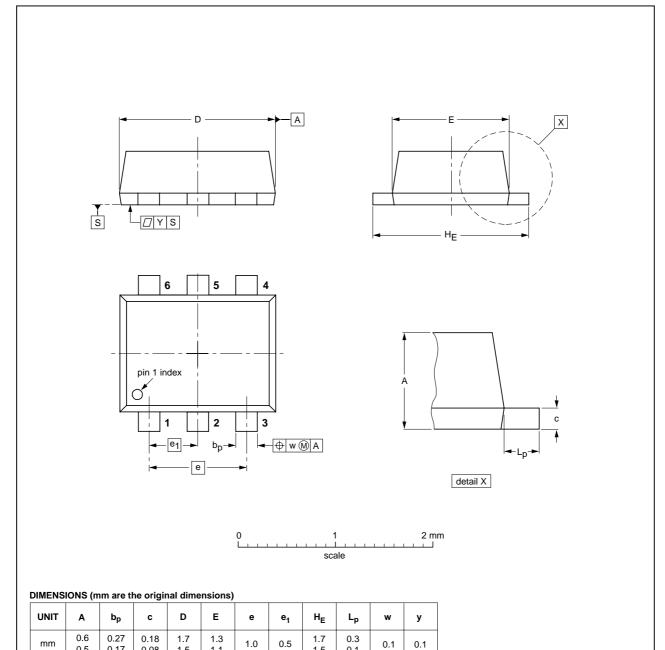
## 15 V low $V_{\text{CE(sat)}}$ NPN double transistor

PBSS2515VS

#### **PACKAGE OUTLINE**

#### Plastic surface-mounted package; 6 leads

**SOT666** 



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT666						<del>-04-11-08-</del> 06-03-16

### 15 V low V<sub>CE(sat)</sub> NPN double transistor

PBSS2515VS

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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